Miniature Surface Mount

LED-OPR5200

Phototransistor—OPR5500



Features:

- Stackable on 2 mm centers
- Vertical or horizontal mounting
- Automatic pick-and-place compatible
- Combine OPR5200 and OPR5500 to create miniature switch



Description:

The **OPR5200** is a miniature high efficiency GaAlAs light emitting diode in a high temperature polyamide chip carrier that is well suited to space-limited applications which require close channel spacing.

The **OPR5500** is a miniature NPN silicon phototransistor housed in a high temperature polyamide chip carrier that is well suited to space-limited applications which require close channel spacing.

When combing the OPR5200 and OPR5500 (miniature phototransistor), this lateral mounting option can be used to create a non-focused reflective or slotted switch configuration.

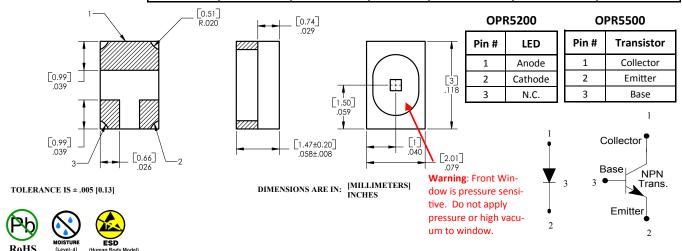
These parts can be automatically placed with standard SMD equipment and can be reflow soldered by virtually any conventional means. Wraparound contacts allow it to be mounted face up or on edge for a beam direction parallel to the seating plane.

See Application Bulletin 237 for handling instructions

Applications:

- Slotted switches
- Industrial environments
- Space-limited applications

Ordering Information							
Part Number	LED Peak Wavelength	Output Power (μW) Min	I _F (mA) Typ / Max	Total Beam Angle (Degrees)	Rise / Fall Times (nS) Typ	Packaging	
OPR5200	890 nm	350	20 / 50	90	500 / 250	Chip Tray	
Part Number	Sensor	Light Current I _{C(ON)} (μΑ) Min	V _{CE} Max	Input Power E _E (μW/cm²)	Viewing Angle (Degrees)	Packaging	
OPR5500	Transistor	36	30	150	120	Chip Tray	



General Note

TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.

Miniature Surface Mount

LED-OPR5200



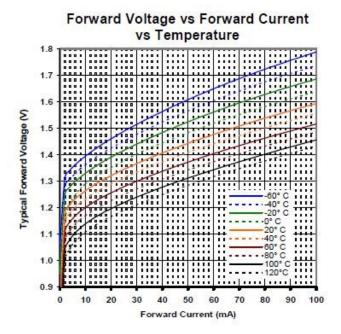
Phototransistor—OPR5500

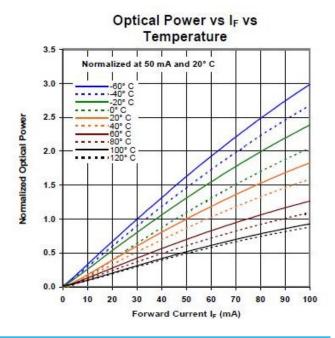
OPR5200 Absolute Maximum Ratings (T _A = 25° C unless otherwise noted)				
Storage and Operating Temperature	-55° C to +125° C			
Continuous Forward Current	50 mA			
Peak Forward Current (1 μs pulse width, 10% duty cycle)	1.0 A			
Power Dissipation ⁽¹⁾	100 mW			
Solder reflow time within 5°C of peak temperature is 20 to 40 seconds (2)	250° C			

DPR5200 Electrical Characteristics (T _A = 25° C unless otherwise noted)							
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS	
Po	Output Power	350	-	-	μW	I _F = 20 mA	
V_{F}	Forward Voltage	-	-	1.8	V	I _F = 20 mA	
I _R	Reverse Current	-	-	100	μΑ	V _R = 2 V	
λ_{P}	Peak Wavelength	-	890	-	nm	I _F = 20 mA	
$\lambda_{\rm BW}$	Spectral Bandwidth	-	80	-	nm	I _F = 20 mA	
θ_{HP}	Emission Angle	-	±45°	-	-	at half power points	
t _r	Output Rise Time	-	500	-	ns	L = 100 mA DW = 10 0 us D C = 100/	
t _f	Output Fall Time	-	250	-	ns	- I _P = 100 mA, PW = 10.0 μs, D.C. = 109	

Notes:

- (1) Derate at 1.00 mW/° C above 25° C.
- (2) Solder time less than 5 seconds at temperature extreme.





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LED-OPR5200

Phototransistor—OPR5500



OPR5500 Absolute Maximum Ratings (T _A = 25° C unless otherwise noted)				
Storage and Operating Temperature	-55° C to +125° C			
Collector-Emitter Voltage	30 V			
Emitter-Collector Voltage	5 V			
Power Dissipation ⁽¹⁾	100 mW			
Solder reflow time within 5°C of peak temperature is 20 to 40 seconds ⁽²⁾	250° C			

Electrical Characteristics (T _A = 25° C unless otherwise noted)							
SYMBOL	PARAMETER		TYP	MAX	UNITS	TEST CONDITIONS	
I _{C(ON)}	On-State Collector Current	36	-	-	μΑ	$V_{CE} = 5 \text{ V}, E_e = 150 \mu\text{W/cm}^2$ (890 nm light source)	
I _{CEO}	Dark Current	-	-	100	nA	$V_{CE} = 5 \text{ V, E}_{e} = 0$	
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage		-	-	V	Ι _C = 100 μΑ	
V _{(BR)ECO}	Emitter-CollectorBreakdown Voltage	5	-	-	V	Ι _Ε = 100 μΑ	
V _(SAT)	Saturation Voltage	-	-	0.4	V	$I_C = 100 \mu A, E_e = 5 \text{ mW/cm}^2$	
t _r , t _f	Output Rise and Fall Time	-	2.5	-	μs	V_{CC} = 5 V, I_C = 800 μ A, R_L = 100 Ω	

Notes:

- (1) Derate at 1.00 mW/° C above 25° C.
- (2) Solder time less than 5 seconds at temperature extreme.

